EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("5849077").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 17:19
S1	10	(("5393681") or ("6391692") or ("5308782") or ("5998248") or ("6319782")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/25 06:43
S2	162	257/929 and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/24 14:45
S3	542	438/300 and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/24 14:44
S4	4	@ad<="20010323" and 'raised vertical lateral transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/04 16:02
S5	1	@ad<="20010323" and 'raised source and drain'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/04 15:26
S6	1	@ad<="20010323" and 'epitaxial' and 'source or drain'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/04 15:30
S7	8	@ad<="20010323" and 'epitaxial' and 'source and drain'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/04 15:30
S8	3470	gardner.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/04 15:45
S9	6	gardner.inv. and 'vertical transistor' and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/04 15:48

S10	4	@ad<="20010323" and 'elevated source and drain'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/25 14:24
S11	257	@ad<="20010323" and 'elevated source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/04 16:06
S12	37	@ad<="20010323" and 'epitaxial' with 'elevated source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/24 14:23
S13	1	"4728623".PN.	USPAT	OR	OFF	2002/09/04 16:31
S14	1	"4738937".PN.	USPAT	OR	OFF	2002/09/04 16:31
S15	1	"4918029".PN.	USPAT	OR	OFF	2002/09/04 16:31
S16	1	"5004702".PN.	USPAT	OR	OFF	2002/09/04 16:31
S17	1	"5030583".PN.	USPAT	OR	OFF	2002/09/04 16:31
S18	1	"5032538".PN.	USPAT	OR	OFF	2002/09/04 16:31
S19	1	"5045494".PN.	USPAT	OR	OFF	2002/09/04 16:31
S20	1	"5272109".PN.	USPAT	OR	OFF	2002/09/04 16:32
S21	1	"5496750".PN.	USPAT	OR	OFF	2002/09/04 16:38
S22	1	"5378651".PN.	USPAT	OR	OFF	2002/09/04 16:38
S23	1	"5321306".PN.	USPAT	OR	OFF	2002/09/04 16:38
S24	1	"5296388".PN.	USPAT	OR	OFF	2002/09/04 16:38
S25	1	"5250454".PN.	USPAT	OR	OFF	2002/09/04 16:39
S26	1	"5213991".PN.	USPAT	OR	OFF	2002/09/04 16:39
S27	1	"5079180".PN.	USPAT	OR	OFF	2002/09/04 16:39
S28	1	"5057899".PN.	USPAT	OR	OFF	2002/09/04 16:39
S29	1	"4966861".PN.	USPAT	OR	OFF	2002/09/04 16:41
S30	1	"4814841".PN.	USPAT	OR	OFF	2002/09/04 16:48
S31	1	"5057893".PN.	USPAT	OR	OFF	2002/09/04 16:48
S32	18	(("6096596") or ("6090691") or ("6057200") or ("6001697") or ("5998844") or ("5963822") or ("5945698") or ("5933738") or ("5863826")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/05 08:23
S33	18	(("5831334") or ("5677573") or ("5641694") or ("5600161") or ("5497017") or ("5312768") or ("5156987") or ("5122476") or ("5087586")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/05 10:18

EAST Search History

S34	2	("5308782").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/05 10:19
S35	2	("6319782").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/05 10:19
S36	1731	((438/300) or (257/302) or (257/929) or (257/592)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/20 08:44
S37	12	ri-seiko.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/20 08:44
S38	38	@ad<="20010323" and 'epitaxial' with 'elevated source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/20 09:33
S39	263	@ad<="20010323" and 'elevated source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/20 09:33
S40	263	@ad<="20010323" and elevated adj1 source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/20 09:02
S41	95	@ad<="20010323" and elevated adj1 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/20 09:02
S42	112	@ad<="20010323" and raised adj1 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/20 09:03
S43	229	@ad<="20010323" and raised adj1 source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/20 09:03

S44	0	@ad<="20010323" and 'epitaxial silicon gate' with 'elevated source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/20 09:38
S45	20	@ad<="20010323" and 'silicon gate' and 'elevated source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/20 09:38
S46	47	@ad<="20010323" and 'polysilicon gate' and 'elevated source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/25 14:14
S47	0	@ad<="20010323" and 'epitaxial polysilicon gate' and 'elevated source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/25 14:25
S48	1	@ad<="20010323" and 'epitaxial polysilicon' and 'elevated source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/20 10:08
S49	56	@ad<="20010323" and 'epitaxial polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/21 08:20
S50	0	@ad<="20010323" and 'epitaxial polysilicon gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/20 14:05
S51	24	@ad<="20010323" and 'epitaxial gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/20 14:05
S52	24	@ad<="20010323" and 'epitaxial gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/21 08:30
S53	560	@ad<="20010323" and polysilicon with epitaxial with gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/20 16:16
S54	2348	@ad<="20010323" and 'multilayer' same 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/21 08:55

S55	260	(@ad<="20010323" and 'multilayer' same 'gate') and 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/20 16:18
S56	0	@ad<="20010323" and 'multilayer gate' with 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 08:33
S57	1	@ad<="20010323" and epitaxial near grow near polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/21 08:20
S58	693	@ad<="20010323" and 'epitaxial silicon' same 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/21 08:32
S59	367	@ad<="20010323" and 'epitaxial silicon' with 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/21 08:41
S60	9	@ad<="20010323" and 'epitaxial silicon gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/26 10:14
S61	1	@ad<="20010323" and 'multilayer silicon gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/21 08:56
S62	1	("6534809").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/03/25 13:55
S63	564	@ad<="20010323" and 'polysilicon gate' same 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/25 14:18
S64	390	(257/756)".ccls" and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/24 14:43

S65	214	@ad<="20010323" and 'floating gate' same 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/25 14:18
S66	2141	@ad<="20010323" and 'elevated' same 'source' and 'drain'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/25 14:28
S67	413	@ad<="20010323" and 'elevated' with 'source' with 'drain'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/25 14:28
S68	6	@ad<="20010323" and 'epi silicon' and 'elevated' same 'source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 06:45
S69	1	"4074300".PN.	USPAT	OR	OFF	2003/03/25 14:37
S70	32	@ad<="20010323" and 'gate stack' and 'elevated' same 'source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/25 15:13
S71	8	(("4583105") or ("6083815") or ("5885877") or ("5986328")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/03/25 15:39
S72	2	("5198378").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/03/25 15:39
S73	92	@ad<="20010323" and 'epi' and 'silicon gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/26 11:54
S74	9	@ad<="20010323" and 'epitaxial silicon gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/26 11:10
S75	1	("6528363").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/03/26 11:10

S76	7	@ad<="20010323" and 'conductor' same 'epi' same 'polysilicon' same 'amorphous'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/26 14:31
S77	0	@ad<="20010323" and 'conductive' same 'epi' same 'polysilicon' same 'amorphous'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/03/26 12:04
S78	3	("6335251").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/03/26 14:34
S79	2	("6232641").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/03/26 15:01
S80	2	("6171910").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/03/26 15:20
S81	2	("6051473").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/03/26 15:20
S82	8	@ad<="20010323" and 'epi silicon' and 'raised' same 'source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/24 14:42
S83	9	@ad<="20010323" and 'epitaxial' adj1 'silicon' adj1 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/24 14:36
S84	24	@ad<="20010323" and 'epitaxial' adj1 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/24 14:36
S85	11	@ad<="20010323" and 'epi silicon' and 'raised' same 'source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/24 14:42

S86	394	(257/756)".ccls" and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 08:50
S87	600	438/300 and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 08:58
S88	2	("6534809").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/25 06:43
S89	173	@ad<="20010323" and 'epitaxial' adj1 'silicon' and 'elevated' same 'source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/18 13:32
S90	2	@ad<="20010323" and 'epitaxial' adj1 'silicon gate' and 'elevated' same 'source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 06:46
S91	43	@ad<="20010323" and 'gate' with 'epitaxial' adj1 'silicon' and 'elevated' same 'source'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 07:35
S92	17	@ad<="20010323" and 'transistor gate' with 'epitaxial' adj1 'silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 07:45
S93	143	@ad<="20010323" and 'transistor gate' with 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 09:33
S94	238	@ad<="20010323" and 'epitaxial' adj2 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 08:08
S95	2	@ad<="20010323" and 'stacked gate' with 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 08:33

S96	243	(438/657).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/18 16:48
S97	225	(438/647).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 08:56
S98	118	(257/385).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 08:56
S99	534	(257/382).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 08:59
S100	225	(438/647).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 08:57
S101	313	(438/300).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 14:23
S102	69	(257/381).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 08:59
S103	244	(257/756).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 10:22
S104	197	@ad<="20010323" and 'polysilicon gate' with 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/25 09:36
S105	0	@ad<="20010323" and 'epitaxial silicon' with 'selected silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 11:35
S106	238	@ad<="20010323" and 'single' with 'poly' with 'amorphous'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 14:09

S10 7	386	@ad<="20010323" and 'epitaxial silicon' with 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 11:42
S10 8	88	@ad<="20010323" and 'gate electrode' with 'epitaxial silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 13:07
S10 9	5	@ad<="20010323" and 'epitaxial' near 'gate' near 'silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 13:11
S11 0	68	@ad<="20010323" and 'epitaxial' near 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 13:19
S11 1	14	@ad<="20010323" and 'epitaxial silicon' near 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 13:19
S11 2	187	@ad<="20010323" and 'epitaxial silicon' near4 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 13:47
S11 3	138	@ad<="20010323" and 'epitaxial silicon' near3 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 13:20
S11 4	2	("6534809").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/12 13:47
S11 5	428	@ad<="20010323" and 'schottky gate' and 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 14:12
S11 6	8	@ad<="20010323" and 'schottky gate' and 'epitaxial silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 14:18

S11 7	1971	@ad<="20010323" and 'epitaxial silicon' near1 'layers'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 14:34
S11 8	13	@ad<="20010323" and 'epitaxial silicon' near1 'layers' near1 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 14:34
S11 9	65	@ad<="20010323" and 'epitaxial silicon' near1 'layers' near2 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 15:11
S12 0	2	("5110748").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/12 15:37
S12 1	1	"3959045".PN.	USPAT	OR	OFF	2003/11/12 15:12
S12 2	1	"3997381".PN.	USPAT	OR	OFF	2003/11/12 15:12
S12 3	1	"4292730".PN.	USPAT	OR	OFF	2003/11/12 15:13
S12 4	1	"4888304".PN.	USPAT	OR	OFF	2003/11/12 15:13
S12 5	1	"4891329".PN.	USPAT	OR	OFF	2003/11/12 15:14
S12 6	1	"4983251".PN.	USPAT	OR	OFF	2003/11/12 15:14
S12 7	1	"5006487".PN.	USPAT	OR	OFF	2003/11/12 15:15
S12 8	1	"5006487".PN.	USPAT	OR	OFF	2003/11/12 15:16
S12 9	1	"5013681".PN.	USPAT	OR	OFF	2003/11/12 15:17
S13 0	0	("candelaria.in.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/12 15:38
S13 1	0	("candelaria-jon.in.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/12 15:37

S13 2	0	("candelaria-jon-j.in.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/12 15:38
S13 3	0	("Candelaria-jon-j.in.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO;` DERWENT; IBM_TDB	OR	OFF	2003/11/12 15:39
S13 4	65	candelaria.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 15:38
S13 5	6	Candelaria-jon-j.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 15:39
S13 6	2	"20020137269"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/18 09:22
S13 7	2	"20020093054"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/18 10:09
S13 8	2	"20010019137"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/18 10:11
S13 9	2	("6630721").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/03/18 10:13
S14 0	2	("6433382").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/03/18 10:26
S14 1	1	"5739567".PN.	USPAT	OR	OFF	2004/03/18 10:19
S14 2	1	"5627395".PN.	USPAT	OR	OFF	2004/03/18 10:34

S143	2	("6150688").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/03/18 10:33
S144	2	("6037202").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/03/18 10:34
S145	22	((("5994735") or ("5886382") or ("5780327") or ("5612563") or ("5612230") or ("5595920") or ("5578850") or ("5574299") or ("4447889") or ("5483094") or ("5460994")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/03/18 10:49
S146	108	@ad<="20010323" and 'vertical' with 'transistor' same 'epitaxial silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 10:06
S147	47	@ad<="20010323" and 'vertical' with 'transistor' with 'epitaxial silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/18 13:34
S148	1480	(257/316).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 14:18
S149	474	(257/303).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 14:18
S150	155	(257/929).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 14:23
S151	51	(438/222).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 14:31
S152	876	(257/368).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 14:27

S153	42	(257/41).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/18 16:54
S154	34	(257/44).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/18 16:56
S155	751	(257/288).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/18 16:57
S156	732	(257/592).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/18 16:57
S157	242	(438/350).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/18 17:00
S158	2	("5888294").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/03/18 17:01
S159	2	"20010040292"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/03/18 17:01
S160	2	("5554870").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 13:33
S161	15	(("5324673") or ("5612230") or ("6150688") or ("5574299") or ("5483094") or ("5460994") or ("5698869") or ("6433382")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 13:47
S162	21	(("6159852") or ("6448129") or ("6458699") or ("6509239") or ("6392271") or ("5578850") or ("5753947") or ("6433382") or ("6018176") or ("5547889") or ("5460994")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 13:48

EAST Search History

S16 3	1489	(257/316).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 14:20
S16 4	485	(257/303).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 14:21
S16 5	319	(438/300).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 14:23
S16 6	155	(257/929).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 14:23
S16 7	884	(257/368).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 10:24
S16 8	51	(438/222).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 14:31
S16 9	78	(438/226).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 14:31
S17 0	72	(438/341).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 14:32
S17 1	212	(438/357).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 14:33
S17 2	23	@ad<="20010323" and 'vertical transistor' same 'epitaxial silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 10:06
S17 3	348	@ad<="20010323" and 'epitaxial silicon' with 'single crystal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 10:27

S17 4	4	@ad<="20010323" and 'vertical' with 'transistor' same 'epitaxial silicon' with 'crystal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 10:15
S17 5	1	"5414287".PN.	USPAT; USOCR	OR	ON	2005/03/10 10:18
S17 6	1	"5350937".PN.	USPAT; USOCR	OR	ON	2005/03/10 10:19
S17 7	1	"5316962".PN.	USPAT; USOCR	OR	ON	2005/03/10 10:19
S17 8	1	"5208172".PN.	USPAT; USOCR	OR	ON	2005/03/10 10:22
S17 9	1	"5316962".PN.	USPAT; USOCR	OR	ON	2005/03/10 10:23
S18 0	1	"5196722".PN.	USPAT; USOCR	OR	ON	2005/03/10 10:23
S18 1	1	"5180680".PN.	USPAT; USOCR	OR	ON	2005/03/10 10:23
S18 2	0	@ad<="20010323" and 'epitaxial silicon structure' with 'single crystal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 10:27
S18 3	1	@ad<="20010323" and 'epitaxial silicon structure' with 'crystal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 10:27
S18 4	7	@ad<="20010323" and 'epitaxial silicon' with 'crystal' with '100' with 'orientation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 10:43
S18 5	0	@ad<="20010323" and 'epitaxial silicon' with 'facet' with '100' with 'orientation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 10:44
S18 6	14	@ad<="20010323" and 'epitaxial silicon' with '100' with 'orientation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 12:57
S18 7	1	@ad<="20010323" and 'epitaxial silicon' with '100' with 'plane orientation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 10:44

S18 8	34	@ad<="20010323" and 'silicon substrate' with '100' with 'orientation' with 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 11:21
S18 9	82	@ad<="20010323" and 'silicon substrate' with '100' with 'orientation' same 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 12:37
S19 0	12	@ad<="20010323" and 'silicon' with 'facet' with '100' same 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 12:58
S19 1	2	@ad<="20010323" and 'epitaxial silicon' with '100' with 'facet'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 12:57
S19 2	0	@ad<="20010323" and 'silicon' same 'orientationt' with '100' same 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 12:58
S19 3	297	@ad<="20010323" and 'silicon' same 'orientation' with '100' same 'epitaxial'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 12:59
S19 4	28	@ad<="20010323" and 'silicon' same 'orientation' with '100' same 'epitaxial silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 12:59
S19 5	3	@ad<="20010323" and 'silicon' same 'orientation' with '100' same 'SEG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 12:59
S19 6	894	(257/330-331).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 10:23
S19 7	439	(257/329).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 10:23
S19 8	398	(257/332-333).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 10:23

S19 9	887	(257/368).ccls. and @ad<="20010323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 10:27
S20 0	2	("4963506").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 10:25
S20 1	26	@ad<="20010323" and 'epitaxial silicon' with 'facet'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 10:30
S20 2	1	@ad<="20010323" and 'epitaxial silicon' with 'facet surface'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 10:27
S20 3	45	@ad<="20010323" and 'epitaxial silicon' same 'facet'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/01 14:01
S20 4	26	@ad<="20010323" and 'SEG' same 'facet'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/01 14:01
S20 5	26	@ad<="20010323" and "SEG" same "facet"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/01 14:04
S20 7	7	@ad<="20010323" and matsumoto. in. and "SEG"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/01 14:39
S20 8	45	@ad<="20010323" and "NEC" and "SEG"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/01 14:48
S20 9	2	"20020137269"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/01 14:47

S21 0	29	@ad<="20010323" and "SEG" same "silicon" same "single" same "crystal"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/01 15:25
S21 1	29	@ad<="20010323" and "SEG" same "single" same "crystal" same "silicon"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/01 17:19
S21 2	1	"5576250".PN.	USPAT; USOCR	OR	ON	2006/03/01 15:27